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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XFI

Product Status	Obsolete
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b820f2048im64-a

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1. Feature List

The EFM32GG11 highlighted features are listed below.

- ARM Cortex-M4 CPU platform
 - High performance 32-bit processor @ up to 72 MHz
 - DSP instruction support and Floating Point Unit
 - Memory Protection Unit
 - Wake-up Interrupt Controller
- Flexible Energy Management System
 - + 80 $\mu\text{A}/\text{MHz}$ in Active Mode (EM0)
 - 2.1 µA EM2 Deep Sleep current (16 kB RAM retention and RTCC running from LFRCO)
- Integrated DC-DC buck converter
- Up to 2048 kB flash program memory
 - · Dual-bank with read-while-write support
- Up to 512 kB RAM data memory
 - 256 kB with ECC (SEC-DED)
- Octal/Quad-SPI Flash Memory Interface
 - Supports 3 V and 1.8 V memories
 - 1/2/4/8-bit data bus
 - Quad-SPI Execute In Place (XIP)
- Communication Interfaces
 - Low-energy Universal Serial Bus (USB) with Device and Host support
 - Fully USB 2.0 compliant
 - On-chip PHY and embedded 5V to 3.3V regulator
 - Crystal-free Device mode operation
 - Patent-pending Low-Energy Mode (LEM)
 - SD/MMC/SDIO Host Controller
 - SD v3.01, SDIO v3.0 and MMC v4.51
 - 1/4/8-bit bus width
 - 10/100 Ethernet MAC with MII/RMII interface
 - IEEE1588-2008 precision time stamping
 - Energy Efficient Ethernet (802.3az)
 - Up to 2× CAN Bus Controller
 - Version 2.0A and 2.0B up to 1 Mbps
 - 6× Universal Synchronous/Asynchronous Receiver/ Transmitter
 - UART/SPI/SmartCard (ISO 7816)/IrDA/I2S/LIN
 - · Triple buffered full/half-duplex operation with flow control
 - Ultra high speed (36 MHz) operation on one instance
 - 2× Universal Asynchronous Receiver/ Transmitter
 - 2× Low Energy UART
 - · Autonomous operation with DMA in Deep Sleep Mode
 - 3× I²C Interface with SMBus support
 - Address recognition in EM3 Stop Mode

- Up to 144 General Purpose I/O Pins
 - Configurable push-pull, open-drain, pull-up/down, input filter, drive strength
 - Configurable peripheral I/O locations
 - 5 V tolerance on select pins
 - Asynchronous external interrupts
 - · Output state retention and wake-up from Shutoff Mode
- Up to 24 Channel DMA Controller
- Up to 24 Channel Peripheral Reflex System (PRS) for autonomous inter-peripheral signaling
- External Bus Interface for up to 4x256 MB of external memory mapped space
 - TFT Controller with Direct Drive
 - Per-pixel alpha-blending engine
- Hardware Cryptography
 - AES 128/256-bit keys
 - ECC B/K163, B/K233, P192, P224, P256
 - SHA-1 and SHA-2 (SHA-224 and SHA-256)
 - True Random Number Generator (TRNG)
- Hardware CRC engine
 - Single-cycle computation with 8/16/32-bit data and 16-bit (programmable)/32-bit (fixed) polynomial
- Security Management Unit (SMU)
 - · Fine-grained access control for on-chip peripherals
- Integrated Low-energy LCD Controller with up to 8×36 segments
 - · Voltage boost, contrast and autonomous animation
 - Patented low-energy LCD driver
- Backup Power Domain
 - RTCC and retention registers in a separate power domain, available down to energy mode EM4H
 - Operation from backup battery when main power absent/ insufficient
- Ultra Low-Power Precision Analog Peripherals
 - 2× 12-bit 1 Msamples/s Analog to Digital Converter (ADC)
 - · On-chip temperature sensor
 - 2× 12-bit 500 ksamples/s Digital to Analog Converter (VDAC)
 - Digital to Analog Current Converter (IDAC)
 - Up to 4× Analog Comparator (ACMP)
 - Up to 4× Operational Amplifier (OPAMP)
 - Robust current-based capacitive sensing with up to 64 inputs and wake-on-touch (CSEN)
 - Up to 108 GPIO pins are analog-capable. Flexible analog peripheral-to-pin routing via Analog Port (APORT)
 - Supply Voltage Monitor

3.2.4 EM2 and EM3 Power Domains

The EFM32GG11 has three independent peripheral power domains for use in EM2 and EM3. Two of these domains are dynamic and can be shut down to save energy. Peripherals associated with the two dynamic power domains are listed in Table 3.1 EM2 and EM3 Peripheral Power Subdomains on page 13. If all of the peripherals in a peripheral power domain are unused, the power domain for that group will be powered off in EM2 and EM3, reducing the overall current consumption of the device. Other EM2, EM3, and EM4-capable peripherals and functions not listed in the table below reside on the primary power domain, which is always on in EM2 and EM3.

Peripheral Power Domain 1	Peripheral Power Domain 2
ACMP0	ACMP1
PCNT0	PCNT1
ADC0	PCNT2
LETIMER0	CSEN
LESENSE	VDAC0
APORT	LEUART0
-	LEUART1
-	LETIMER1
-	12C0
-	12C1
-	12C2
-	IDAC
-	ADC1
-	ACMP2
-	ACMP3
-	LCD
-	RTC

Table 3.1. EM2 and EM3 Peripheral Power Subdomains

3.3 General Purpose Input/Output (GPIO)

EFM32GG11 has up to 144 General Purpose Input/Output pins. GPIO are organized on three independent supply rails, allowing for interface to multiple logic levels in the system simultaneously. Each GPIO pin can be individually configured as either an output or input. More advanced configurations including open-drain, open-source, and glitch-filtering can be configured for each individual GPIO pin. The GPIO pins can be overridden by peripheral connections, like SPI communication. Each peripheral connection can be routed to several GPIO pins on the device. The input value of a GPIO pin can be routed through the Peripheral Reflex System to other peripherals. The GPIO subsystem supports asynchronous external pin interrupts.

3.4 Clocking

3.4.1 Clock Management Unit (CMU)

The Clock Management Unit controls oscillators and clocks in the EFM32GG11. Individual enabling and disabling of clocks to all peripheral modules is performed by the CMU. The CMU also controls enabling and configuration of the oscillators. A high degree of flexibility allows software to optimize energy consumption in any specific application by minimizing power dissipation in unused peripherals and oscillators.

3.8.4 Capacitive Sense (CSEN)

The CSEN module is a dedicated Capacitive Sensing block for implementing touch-sensitive user interface elements such a switches and sliders. The CSEN module uses a charge ramping measurement technique, which provides robust sensing even in adverse conditions including radiated noise and moisture. The module can be configured to take measurements on a single port pin or scan through multiple pins and store results to memory through DMA. Several channels can also be shorted together to measure the combined capacitance or implement wake-on-touch from very low energy modes. Hardware includes a digital accumulator and an averaging filter, as well as digital threshold comparators to reduce software overhead.

3.8.5 Digital to Analog Current Converter (IDAC)

The Digital to Analog Current Converter can source or sink a configurable constant current. This current can be driven on an output pin or routed to the selected ADC input pin for capacitive sensing. The full-scale current is programmable between 0.05 μ A and 64 μ A with several ranges consisting of various step sizes.

3.8.6 Digital to Analog Converter (VDAC)

The Digital to Analog Converter (VDAC) can convert a digital value to an analog output voltage. The VDAC is a fully differential, 500 ksps, 12-bit converter. The opamps are used in conjunction with the VDAC, to provide output buffering. One opamp is used per singleended channel, or two opamps are used to provide differential outputs. The VDAC may be used for a number of different applications such as sensor interfaces or sound output. The VDAC can generate high-resolution analog signals while the MCU is operating at low frequencies and with low total power consumption. Using DMA and a timer, the VDAC can be used to generate waveforms without any CPU intervention. The VDAC is available in all energy modes down to and including EM3.

3.8.7 Operational Amplifiers

The opamps are low power amplifiers with a high degree of flexibility targeting a wide variety of standard opamp application areas, and are available down to EM3. With flexible built-in programming for gain and interconnection they can be configured to support multiple common opamp functions. All pins are also available externally for filter configurations. Each opamp has a rail to rail input and a rail to rail output. They can be used in conjunction with the VDAC module or in stand-alone configurations. The opamps save energy, PCB space, and cost as compared with standalone opamps because they are integrated on-chip.

3.8.8 Liquid Crystal Display Driver (LCD)

The LCD driver is capable of driving a segmented LCD display with up to 8x36 segments. A voltage boost function enables it to provide the LCD display with higher voltage than the supply voltage for the device. A patented charge redistribution driver can reduce the LCD module supply current by up to 40%. In addition, an animation feature can run custom animations on the LCD display without any CPU intervention. The LCD driver can also remain active even in Energy Mode 2 and provides a Frame Counter interrupt that can wake-up the device on a regular basis for updating data.

3.9 Reset Management Unit (RMU)

The RMU is responsible for handling reset of the EFM32GG11. A wide range of reset sources are available, including several power supply monitors, pin reset, software controlled reset, core lockup reset, and watchdog reset.

3.10 Core and Memory

3.10.1 Processor Core

The ARM Cortex-M processor includes a 32-bit RISC processor integrating the following features and tasks in the system:

- ARM Cortex-M4 RISC processor with FPU achieving 1.25 Dhrystone MIPS/MHz
- Memory Protection Unit (MPU) supporting up to 8 memory segments
- Embedded Trace Macrocell (ETM) for real-time trace and debug
- Up to 2048 kB flash program memory
 - · Dual-bank memory with read-while-write support
- Up to 512 kB RAM data memory
- · Configuration and event handling of all modules
- · 2-pin Serial-Wire or 4-pin JTAG debug interface

4.1.2 Operating Conditions

When assigning supply sources, the following requirements must be observed:

- VREGVDD must be greater than or equal to AVDD, DVDD and all IOVDD supplies.
- VREGVDD = AVDD
- DVDD ≤ AVDD
- IOVDD ≤ AVDD

4.1.10 Oscillators

4.1.10.1 Low-Frequency Crystal Oscillator (LFXO)

Table 4.12.	Low-Frequency Crystal Oscillator (LFXO)
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Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Crystal frequency	f _{LFXO}		_	32.768	_	kHz
Supported crystal equivalent series resistance (ESR)	ESR _{LFXO}		_	_	70	kΩ
Supported range of crystal load capacitance ¹	C _{LFXO_CL}		6	_	18	pF
On-chip tuning cap range ²	C _{LFXO_T}	On each of LFXTAL_N and LFXTAL_P pins	8	_	40	pF
On-chip tuning cap step size	SS _{LFXO}		_	0.25	_	pF
Current consumption after startup ³	I _{LFXO}	ESR = 70 kOhm, C_L = 7 pF, GAIN ⁴ = 2, AGC ⁴ = 1	_	273	_	nA
Start- up time	t _{LFXO}	ESR = 70 kOhm, C _L = 7 pF, GAIN ⁴ = 2	_	308	_	ms

Note:

1. Total load capacitance as seen by the crystal.

2. The effective load capacitance seen by the crystal will be C_{LFXO_T} /2. This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal.

3. Block is supplied by AVDD if ANASW = 0, or DVDD if ANASW=1 in EMU_PWRCTRL register.

4. In CMU_LFXOCTRL register.

4.1.12 General-Purpose I/O (GPIO)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Input low voltage	V _{IL}	GPIO pins	_		IOVDD*0.3	V
Input high voltage	V _{IH}	GPIO pins	IOVDD*0.7	_	_	V
Output high voltage relative	V _{OH}	Sourcing 3 mA, IOVDD \ge 3 V,	IOVDD*0.8	_	_	V
to IOVDD		DRIVESTRENGTH ¹ = WEAK				
		Sourcing 1.2 mA, IOVDD \ge 1.62 V,	IOVDD*0.6	—	-	V
		DRIVESTRENGTH ¹ = WEAK				
		Sourcing 20 mA, IOVDD \ge 3 V,	IOVDD*0.8	_	_	V
		DRIVESTRENGTH ¹ = STRONG				
		Sourcing 8 mA, IOVDD ≥ 1.62 V,	IOVDD*0.6	—	_	V
		DRIVESTRENGTH ¹ = STRONG				
Output low voltage relative to	V _{OL}	Sinking 3 mA, IOVDD ≥ 3 V,	_	—	IOVDD*0.2	V
IOVDD		DRIVESTRENGTH ¹ = WEAK				
		Sinking 1.2 mA, IOVDD \ge 1.62 V,	_	_	IOVDD*0.4	V
		DRIVESTRENGTH ¹ = WEAK				
		Sinking 20 mA, IOVDD \ge 3 V,	_	_	IOVDD*0.2	V
		DRIVESTRENGTH ¹ = STRONG				
		Sinking 8 mA, IOVDD ≥ 1.62 V,	_	_	IOVDD*0.4	V
		DRIVESTRENGTH ¹ = STRONG				
Input leakage current	I _{IOLEAK}	All GPIO except LFXO pins, GPIO ≤ IOVDD, T ≤ 85 °C	—	0.1	TBD	nA
		LFXO Pins, GPIO ≤ IOVDD, T ≤ 85 °C	—	0.1	TBD	nA
		All GPIO except LFXO pins, GPIO ≤ IOVDD, T > 85 °C	—		TBD	nA
		LFXO Pins, GPIO ≤ IOVDD, T > 85 °C	—	_	TBD	nA
Input leakage current on 5VTOL pads above IOVDD	I _{5VTOLLEAK}	IOVDD < GPIO ≤ IOVDD + 2 V	-	3.3	TBD	μA
I/O pin pull-up/pull-down re- sistor	R _{PUD}		TBD	40	TBD	kΩ
Pulse width of pulses re- moved by the glitch suppres- sion filter	t _{IOGLITCH}		15	25	35	ns

Table 4.20. General-Purpose I/O (GPIO)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Signal to noise and distortion ratio (1 kHz sine wave),	SNDR _{DAC}	500 ksps, single-ended, internal 1.25V reference	_	60.4	_	dB
Noise band limited to 250 kHz		500 ksps, single-ended, internal 2.5V reference	—	61.6	_	dB
		500 ksps, single-ended, 3.3V VDD reference	_	64.0	_	dB
		500 ksps, differential, internal 1.25V reference	_	63.3	_	dB
		500 ksps, differential, internal 2.5V reference	_	64.4	_	dB
		500 ksps, differential, 3.3V VDD reference	_	65.8	_	dB
Signal to noise and distortion ratio (1 kHz sine wave),	SNDR _{DAC_BAND}	500 ksps, single-ended, internal 1.25V reference	—	65.3	_	dB
Noise band limited to 22 kHz		500 ksps, single-ended, internal 2.5V reference	_	66.7	_	dB
		500 ksps, differential, 3.3V VDD reference	_	68.5	_	dB
		500 ksps, differential, internal 1.25V reference	_	67.8	_	dB
		500 ksps, differential, internal 2.5V reference	_	69.0	_	dB
		500 ksps, single-ended, 3.3V VDD reference	_	70.0	_	dB
Total harmonic distortion	THD		_	70.2	_	dB
Differential non-linearity ³	DNL _{DAC}		TBD	_	TBD	LSB
Intergral non-linearity	INL _{DAC}		TBD		TBD	LSB
Offset error ⁵	V _{OFFSET}	T = 25 °C	TBD	_	TBD	mV
		Across operating temperature range	TBD		TBD	mV
Gain error ⁵	V _{GAIN}	T = 25 °C, Low-noise internal ref- erence (REFSEL = 1V25LN or 2V5LN)	TBD	_	TBD	%
		Across operating temperature range, Low-noise internal refer- ence (REFSEL = 1V25LN or 2V5LN)	TBD		TBD	%
External load capactiance, OUTSCALE=0	C _{LOAD}		_	_	75	pF

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Open-loop gain	G _{OL}	DRIVESTRENGTH = 3	_	135	_	dB
		DRIVESTRENGTH = 2	—	137	_	dB
		DRIVESTRENGTH = 1	_	121	_	dB
		DRIVESTRENGTH = 0	—	109	_	dB
Loop unit-gain frequency ⁷	UGF	DRIVESTRENGTH = 3, Buffer connection	_	3.38	_	MHz
		DRIVESTRENGTH = 2, Buffer connection	_	0.9	_	MHz
		DRIVESTRENGTH = 1, Buffer connection	_	132	_	kHz
		DRIVESTRENGTH = 0, Buffer connection	_	34		kHz
		DRIVESTRENGTH = 3, 3x Gain connection	_	2.57	_	MHz
		DRIVESTRENGTH = 2, 3x Gain connection	_	0.71	_	MHz
		DRIVESTRENGTH = 1, 3x Gain connection	_	113	_	kHz
		DRIVESTRENGTH = 0, 3x Gain connection	_	28	_	kHz
Phase margin	PM	DRIVESTRENGTH = 3, Buffer connection		67	_	0
		DRIVESTRENGTH = 2, Buffer connection	_	69	_	0
		DRIVESTRENGTH = 1, Buffer connection	_	63	_	0
		DRIVESTRENGTH = 0, Buffer connection	_	68	_	0
Output voltage noise	N _{OUT}	DRIVESTRENGTH = 3, Buffer connection, 10 Hz - 10 MHz	_	146	_	µVrms
		DRIVESTRENGTH = 2, Buffer connection, 10 Hz - 10 MHz	_	163	_	µVrms
		DRIVESTRENGTH = 1, Buffer connection, 10 Hz - 1 MHz	_	170	_	μVrms
		DRIVESTRENGTH = 0, Buffer connection, 10 Hz - 1 MHz	_	176	_	µVrms
		DRIVESTRENGTH = 3, 3x Gain connection, 10 Hz - 10 MHz	_	313	_	µVrms
		DRIVESTRENGTH = 2, 3x Gain connection, 10 Hz - 10 MHz	_	271	_	µVrms
		DRIVESTRENGTH = 1, 3x Gain connection, 10 Hz - 1 MHz	_	247	_	μVrms
		DRIVESTRENGTH = 0, 3x Gain connection, 10 Hz - 1 MHz	-	245	-	μVrms

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
SCLK period ^{1 3 2}	t _{SCLK}		6 * ^t HFPERCLK	_	—	ns
SCLK high time ^{1 3 2}	t _{SCLK_HI}		2.5 * ^t HFPERCLK	—	_	ns
SCLK low time ^{1 3 2}	t _{SCLK_LO}		2.5 * ^t HFPERCLK	—	_	ns
CS active to MISO ^{1 3}	t _{cs_аст_мі}		24	—	69	ns
CS disable to MISO ^{1 3}	t _{CS_DIS_MI}		19	_	175	ns
MOSI setup time ^{1 3}	t _{SU_MO}		7	—	—	ns
MOSI hold time ^{1 3 2}	t _{H_MO}		6	_	—	ns
SCLK to MISO ^{1 3 2}	t _{SCLK_MI}		16 + 1.5 * ^t HFPERCLK	_	43 + 2.5 * t _{HFPERCLK}	ns

Table 4.35. SPI Slave Timing

Note:

1. Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0).

2. t_{HFPERCLK} is one period of the selected HFPERCLK.

3. Measurement done with 8 pF output loading at 10% and 90% of V_{DD} (figure shows 50% of V_{DD}).

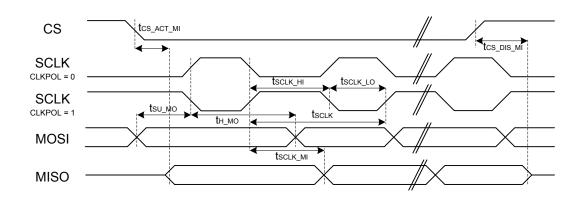


Figure 4.2. SPI Slave Timing Diagram

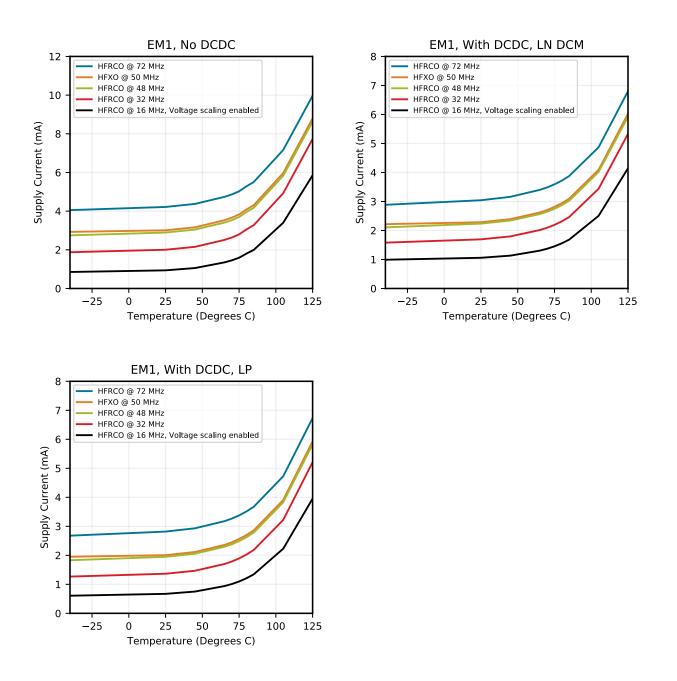


Figure 4.25. EM1 Sleep Mode Typical Supply Current vs. Temperature

Typical supply current for EM2, EM3 and EM4H using standard software libraries from Silicon Laboratories.

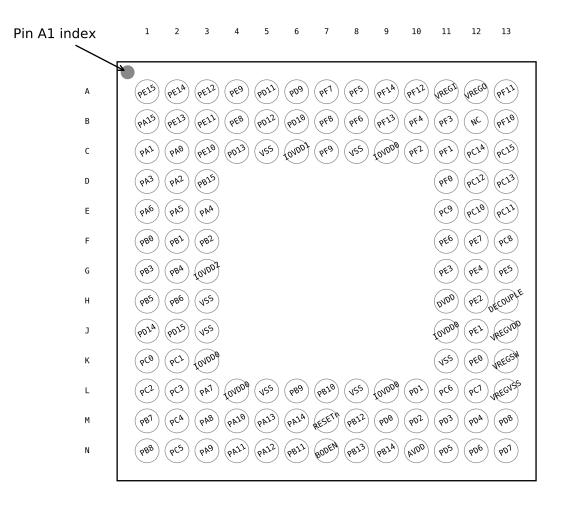


Figure 5.4. EFM32GG11B5xx in BGA120 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Table 5.4.	EFM32GG11B5xx in BGA120 Device Pinout
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Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE15	A1	GPIO	PE14	A2	GPIO
PE12	A3	GPIO	PE9	A4	GPIO
PD11	A5	GPIO	PD9	A6	GPIO
PF7	A7	GPIO	PF5	A8	GPIO
PF14	A9	GPIO (5V)	PF12	A10	GPIO
VREGI	A11	Input to 5 V regulator.	VREGO	A12	Decoupling for 5 V regulator and regu- lator output. Power for USB PHY in USB-enabled OPNs

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PF2	78	GPIO	NC	79	No Connect.
PF12	80	GPIO	PF5	81	GPIO
PF6	84	GPIO	PF7	85	GPIO
PF8	86	GPIO	PF9	87	GPIO
PD9	88	GPIO	PD10	89	GPIO
PD11	90	GPIO	PD12	91	GPIO
PE8	92	GPIO	PE9	93	GPIO
PE10	94	GPIO	PE11	95	GPIO
PE12	96	GPIO	PE13	97	GPIO
PE14	98	GPIO	PE15	99	GPIO
PA15	100	GPIO			
Note:		·]			

1. GPIO with 5V tolerance are indicated by (5V).

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PB2	11	GPIO	PB3	12	GPIO
PB4	13	GPIO	PB5	14	GPIO
PB6	15	GPIO	VSS	16 32 58 83	Ground
PC0	18	GPIO (5V)	PC1	19	GPIO (5V)
PC2	20	GPIO (5V)	PC3	21	GPIO (5V)
PC4	22	GPIO	PC5	23	GPIO
PB7	24	GPIO	PB8	25	GPIO
PA7	26	GPIO	PA8	27	GPIO
PA9	28	GPIO	PA10	29	GPIO
PA11	30	GPIO	PA12	33	GPIO (5V)
PA13	34	GPIO (5V)	PA14	35	GPIO
RESETn	36	Reset input, active low. To apply an ex- ternal reset source to this pin, it is re- quired to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.	PB9	37	GPIO (5V)
PB10	38	GPIO (5V)	PB11	39	GPIO
PB12	40	GPIO	AVDD	41 45	Analog power supply.
PB13	42	GPIO	PB14	43	GPIO
PD0	46	GPIO (5V)	PD1	47	GPIO
PD2	48	GPIO (5V)	PD3	49	GPIO
PD4	50	GPIO	PD5	51	GPIO
PD6	52	GPIO	PD7	53	GPIO
PD8	54	GPIO	PC6	55	GPIO
PC7	56	GPIO	DVDD	57	Digital power supply.
DECOUPLE	59	Decouple output for on-chip voltage regulator. An external decoupling capacitor is required at this pin.	PE0	60	GPIO (5V)
PE1	61	GPIO (5V)	PE2	62	GPIO
PE3	63	GPIO	PE4	64	GPIO
PE5	65	GPIO	PE6	66	GPIO
PE7	67	GPIO	PC8	68	GPIO (5V)
PC9	69	GPIO (5V)	PC10	70	GPIO (5V)
PC11	71	GPIO (5V)	PC12	72	GPIO (5V)
PC13	73	GPIO (5V)	PC14	74	GPIO (5V)
PC15	75	GPIO (5V)	PF0	76	GPIO (5V)
PF1	77	GPIO (5V)	PF2	78	GPIO

Alternate	LOC	ATION	
Functionality	0 - 3	4 - 7	Description
LES_CH11	0: PC11		LESENSE channel 11.
LES_CH12	0: PC12		LESENSE channel 12.
LES_CH13	0: PC13		LESENSE channel 13.
LES_CH14	0: PC14		LESENSE channel 14.
LES_CH15	0: PC15		LESENSE channel 15.
LETIM0_OUT0	0: PD6 1: PB11 2: PF0 3: PC4	4: PE12 5: PC14 6: PA8 7: PB9	Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	0: PD7 1: PB12 2: PF1 3: PC5	4: PE13 5: PC15 6: PA9 7: PB10	Low Energy Timer LETIM0, output channel 1.
LETIM1_OUT0	0: PA7 1: PA11 2: PA12 3: PC2	4: PB5 5: PB2 6: PG0 7: PG2	Low Energy Timer LETIM1, output channel 0.
LETIM1_OUT1	0: PA6 1: PA13 2: PA14 3: PC3	4: PB6 5: PB1 6: PG1 7: PG3	Low Energy Timer LETIM1, output channel 1.
LEU0_RX	0: PD5 1: PB14 2: PE15 3: PF1	4: PA0 5: PC15	LEUART0 Receive input.
LEU0_TX	0: PD4 1: PB13 2: PE14 3: PF0	4: PF2 5: PC14	LEUART0 Transmit output. Also used as receive input in half duplex communication.
LEU1_RX	0: PC7 1: PA6 2: PD3 3: PB1	4: PB5 5: PH1	LEUART1 Receive input.
LEU1_TX	0: PC6 1: PA5 2: PD2 3: PB0	4: PB4 5: PH0	LEUART1 Transmit output. Also used as receive input in half duplex communication.

Alternate	LOC	ATION	
Functionality	0 - 3	4 - 7	Description
US5_RX	0: PE9 1: PA7 2: PB1 3: PH11		USART5 Asynchronous Receive. USART5 Synchronous mode Master Input / Slave Output (MISO).
US5_TX	0: PE8 1: PA6 2: PF15 3: PH10		USART5 Asynchronous Transmit. Also used as receive input in half duplex communica- tion. USART5 Synchronous mode Master Output / Slave Input (MOSI).
USB_DM	0: PF10		USB D- pin.
USB_DP	0: PF11		USB D+ pin.
USB_ID	0: PF12		USB ID pin.
USB_VBUSEN	0: PF5		USB 5 V VBUS enable.
VDAC0_EXT	0: PD6		Digital to analog converter VDAC0 external reference input pin.
VDAC0_OUT0 / OPA0_OUT	0: PB11		Digital to Analog Converter DAC0 output channel number 0.
VDAC0_OUT0ALT / OPA0_OUTALT	0: PC0 1: PC1 2: PC2 3: PC3	4: PD0	Digital to Analog Converter DAC0 alternative output for channel 0.
VDAC0_OUT1 / OPA1_OUT	0: PB12		Digital to Analog Converter DAC0 output channel number 1.
VDAC0_OUT1ALT / OPA1_OUTALT	0: PC12 1: PC13 2: PC14 3: PC15	4: PD1	Digital to Analog Converter DAC0 alternative output for channel 1.
WTIM0_CC0	0: PE4 1: PA6 2: PG2 3: PG8	4: PC15 5: PB0 6: PB3 7: PC1	Wide timer 0 Capture Compare input / output channel 0.
WTIM0_CC1	0: PE5 1: PD13 2: PG3 3: PG9	4: PF0 5: PB1 6: PB4 7: PC2	Wide timer 0 Capture Compare input / output channel 1.

Dimension	Min	Тур	Мах	
A	0.78	0.84	0.90	
A1	0.13	0.18	0.23	
A3	0.17	0.21	0.25	
A2	0.45 REF			
D	7.00 BSC			
е	0.50 BSC			
E	7.00 BSC			
D1	6.00 BSC			
E1	6.00 BSC			
b	0.20	0.25	0.30	
ааа	0.10			
bbb	0.10			
ddd	0.08			
еее	0.15			
fff	0.05			
Noto	1			

Table 8.1. BGA120 Package Dimensions

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.

2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.

3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

Table 8.2. BGA120 PCB Land Pattern Dimensions

Min	Nom	Мах
	0.20	
	6.00	
	6.00	
	0.5	
	0.5	
	Min	0.20 6.00 6.00 0.5

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.

2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification.

3. This Land Pattern Design is based on the IPC-7351 guidelines.

4. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 μm minimum, all the way around the pad.

5. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.

6. The stencil thickness should be 0.125 mm (5 mils).

7. The ratio of stencil aperture to land pad size should be 1:1.

8. A No-Clean, Type-3 solder paste is recommended.

9. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.



Figure 8.3. BGA120 Package Marking

The package marking consists of:

- PPPPPPPPP The part number designation.
- TTTTTT A trace or manufacturing code. The first letter is the device revision.
- YY The last 2 digits of the assembly year.
- WW The 2-digit workweek when the device was assembled.

Table 10.2. TQFP100 PCB Land Pattern Dimensions

Min	Nom	Мах
	15.4	
15.4		
0.50 BSC		
	0.30	
	1.50	
	Min	15.4 15.4 0.50 BSC 0.30

Note:

- 1. All dimensions shown are in millimeters (mm) unless otherwise noted.
- 2. This Land Pattern Design is based on the IPC-7351 guidelines.
- 3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
- 4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release. 5. The stencil thickness should be 0.125 mm (5 mils).
- 6. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.
- 7. A No-Clean, Type-3 solder paste is recommended.
- 8. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

10.3 TQFP100 Package Marking



Figure 10.3. TQFP100 Package Marking

The package marking consists of:

- PPPPPPPP The part number designation.
- TTTTTT A trace or manufacturing code. The first letter is the device revision.
- YY The last 2 digits of the assembly year.
- · WW The 2-digit workweek when the device was assembled.

Dimension	Min	Тур	Мах	
A	_	1.15	1.20	
A1	0.05	—	0.15	
A2	0.95	1.00	1.05	
b	0.17	0.22	0.27	
b1	0.17	0.20	0.23	
С	0.09	_	0.20	
c1	0.09	—	0.16	
D	12.00 BSC			
D1	10.00 BSC			
e	0.50 BSC			
E	12.00 BSC			
E1		10.00 BSC		
L	0.45	0.60	0.75	
L1		1.00 REF		
R1	0.08	—	—	
R2	0.08	_	0.20	
S	0.20	—	—	
θ	0	3.5	7	
θ1	0	—	0.10	
θ2	11	12	13	
θ3	11	12	13	
Note:	· ·	· ·		

Table 11.1. TQFP64 Package Dimensions

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.

2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.

3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.